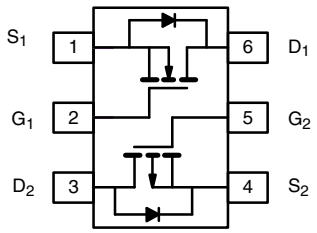
Complementary N- and P-Channel 60 V (D-S) MOSFET

PRODUCT SUMMARY			
	V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (mA)
N-Channel	60	1.40 at V_{GS} = 10 V	500
		3 at V_{GS} = 4.5 V	200
P-Channel	- 60	4 at V_{GS} = - 10 V	- 500
		8 at V_{GS} = - 4.5 V	- 25

SC-89



Top View

Marking Code: H

Ordering Information: Si1029X-T1-GE3 (Lead (Pb)-free and Halogen-free)

FEATURES

- **Halogen-free According to IEC 61249-2-21 Definition**
- TrenchFET® Power MOSFETs
- Very Small Footprint
- High-Side Switching
- Low On-Resistance:
  N-Channel, 1.40 Ω
  P-Channel, 4 Ω
- Low Threshold: ± 2 V (typ.)
- Fast Switching Speed: 15 ns (typ.)
- Gate-Source ESD Protected: 2000 V
- Compliant to RoHS Directive 2002/95/EC

Pb-free
RoHS COMPLIANT
HALOGEN FREE

BENEFITS

- Ease in Driving Switches
- Low Offset (Error) Voltage
- Low-Voltage Operation
- High-Speed Circuits

APPLICATIONS

- Replace Digital Transistor, Level-Shifter
- Battery Operated Systems
- Power Supply Converter Circuits

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise noted)

Parameter		Symbol	N-Channel		P-Channel		Unit
			5 s	Steady State	5 s	Steady State	
Drain-Source Voltage		V_{DS}	60		- 60		V
Gate-Source Voltage		V_{GS}	± 20				
Continuous Drain Current (T_J = 150 °C)[a]	T_A = 25 °C	I_D	320	305	- 200	- 190	mA
	T_A = 85 °C		230	220	- 145	- 135	
Pulsed Drain Current[b]		I_{DM}	650		- 650		
Continuous Source Current (Diode Conduction)[a]		I_S	450	380	- 450	- 380	
Maximum Power Dissipation[a]	T_A = 25 °C	P_D	280	250	280	250	mW
	T_A = 85 °C		145	130	145	130	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150				°C
Gate-Source ESD Rating (HBM, Method 3015)		ESD	2000				V

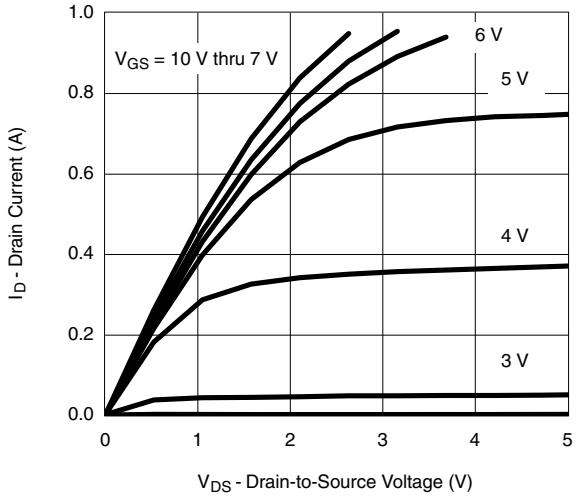
Notes:
a. Surface mounted on FR4 board.
b. Pulse width limited by maximum junction temperature.

SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)							
Parameter	**Symbol**	**Test Conditions**		**Min.**	**Typ.**	**Max.**	**Unit**
Static							
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = 10 µA	N-Ch	60			V
		V_{GS} = 0 V, I_D = - 10 µA	P-Ch	- 60			
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA	N-Ch	1		2.5	
		V_{DS} = V_{GS}, I_D = - 250 µA	P-Ch	- 1		- 3.0	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 5 V	N-Ch			± 50	nA
			P-Ch			± 100	
		V_{DS} = 0 V, V_{GS} = ± 10 V	N-Ch			± 150	
			P-Ch			± 200	
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 50 V, V_{GS} = 0 V	N-Ch			10	
		V_{DS} = - 50 V, V_{GS} = 0 V	P-Ch			- 25	
		V_{DS} = 50 V, V_{GS} = 0 V, T_J = 85 °C	N-Ch			100	
		V_{DS} = - 50 V, V_{GS} = 0 V, T_J = 85 °C	P-Ch			- 250	
On-State Drain Current[a]	$I_{D(on)}$	V_{DS} = 10 V, V_{GS} = 4.5 V	N-Ch	500			mA
		V_{DS} = - 10 V, V_{GS} = - 4.5 V	P-Ch	- 50			
		V_{DS} = 7.5 V, V_{GS} = - 4.5 V	N-Ch	800			
		V_{DS} = - 10 V, V_{GS} = - 10 V	P-Ch	- 600			
Drain-Source On-State Resistance[a]	$R_{DS(on)}$	V_{GS} = 4.5 V, I_D = 200 mA	N-Ch			3	Ω
		V_{GS} = - 4.5 V, I_D = - 25 mA	P-Ch			8	
		V_{GS} = 10 V, I_D = 500 mA	N-Ch			1.40	
		V_{GS} = - 10 V, I_D = - 500 mA	P-Ch			4	
		V_{GS} = 10 V, I_D = 500 mA, T_J = 125 °C	N-Ch			2.50	
		V_{GS} = - 10 V, I_D = - 500 mA, T_J = 125 °C	P-Ch			6	
Forward Transconductance[a]	g_{fs}	V_{DS} = 10 V, I_D = 200 mA	N-Ch		200		ms
		V_{DS} = - 10 V, I_D = - 100 mA	P-Ch		100		
Diode Forward Voltage[a]	V_{SD}	I_S = 200 mA, V_{GS} = 0 V	N-Ch			1.4	V
		I_S = - 200 mA, V_{GS} = 0 V	P-Ch			- 1.4	
Dynamic[b]							
Total Gate Charge	Q_g	N-Channel V_{DS} = 10 V, V_{GS} = 4.5 V, I_D = 250 mA P-Channel V_{DS} = - 30 V, V_{GS} = - 15 V, I_D = - 500 mA	N-Ch		750		pC
			P-Ch		1700		
Gate-Source Charge	Q_{gs}		N-Ch		75		
			P-Ch		260		
Gate-Drain Charge	Q_{gd}		N-Ch		225		
			P-Ch		460		
Input Capacitance	C_{iss}	N-Channel V_{DS} = 25 V, V_{GS} = 0 V, f = 1 MHz P-Channel V_{DS} = - 25 V, V_{GS} = 0 V, f = 1 MHz	N-Ch		30		pF
			P-Ch		23		
Output Capacitance	C_{oss}		N-Ch		6		
			P-Ch		10		
Reverse Transfer Capacitance	C_{rss}		N-Ch		3		
			P-Ch		5		
Turn-On Time[c]	t_{ON}	N-Channel V_{DD} = 30 V, R_L = 150 Ω I_D ≅ 200 mA, V_{GEN} = 10 V, R_g = 10 Ω	N-Ch		15		ns
			P-Ch		20		
Turn-Off Time[c]	t_{OFF}	P-Channel V_{DD} = - 25 V, R_L = 150 Ω I_D ≅ - 165 mA, V_{GEN} = - 10 V, R_g = 10 Ω	N-Ch		20		
			P-Ch		35		

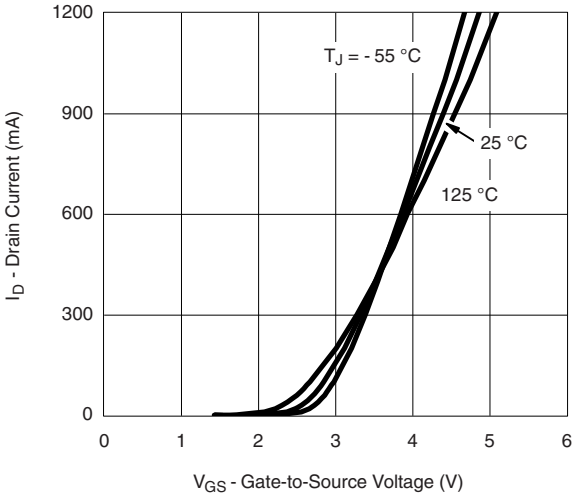
Notes:
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.
c. Switching time is essentially independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

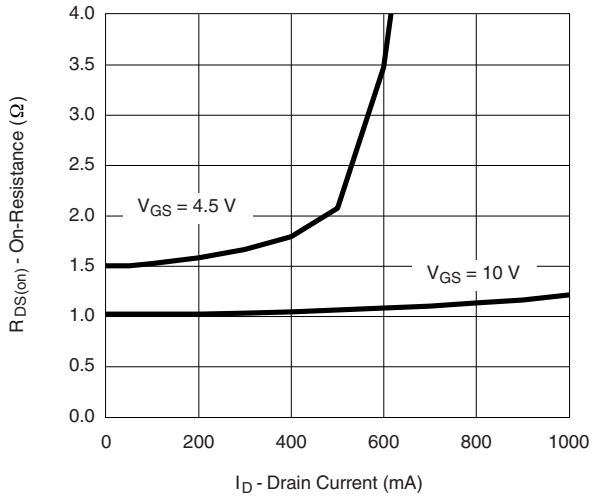
N-CHANNEL TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



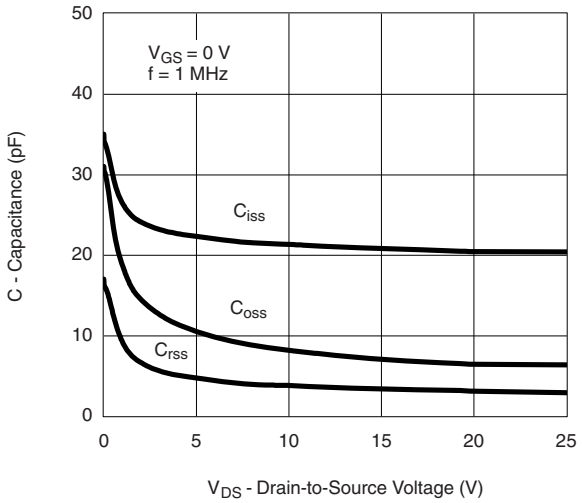
Output Characteristics



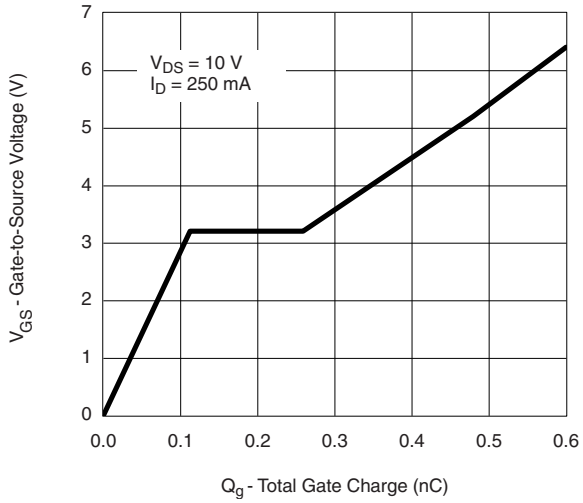
Transfer Characteristics



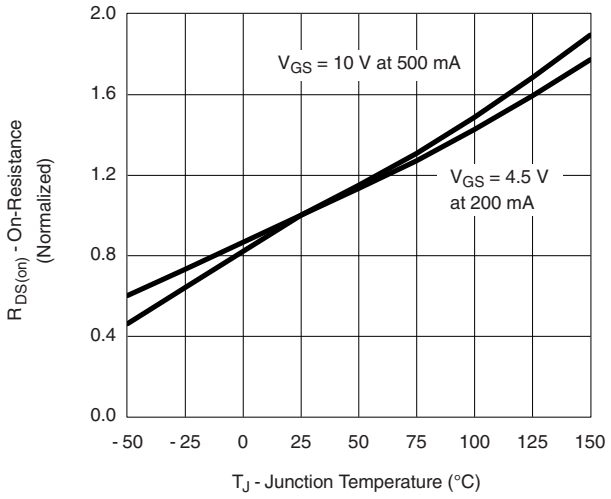
On-Resistance vs. Drain Current



Capacitance

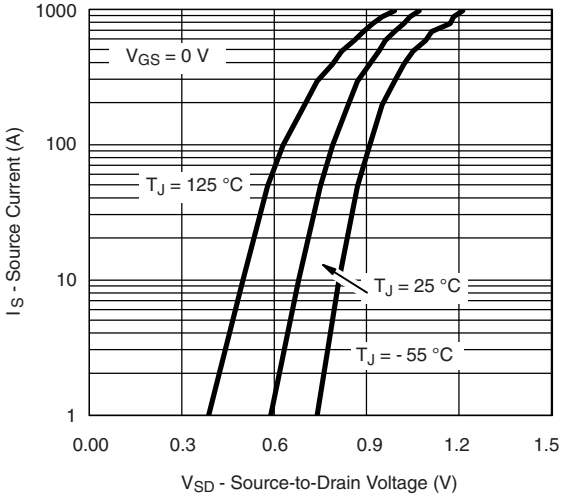


Gate Charge

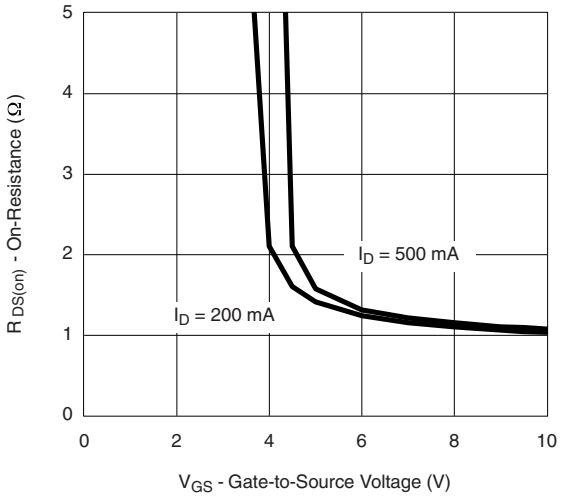


On-Resistance vs. Junction Temperature

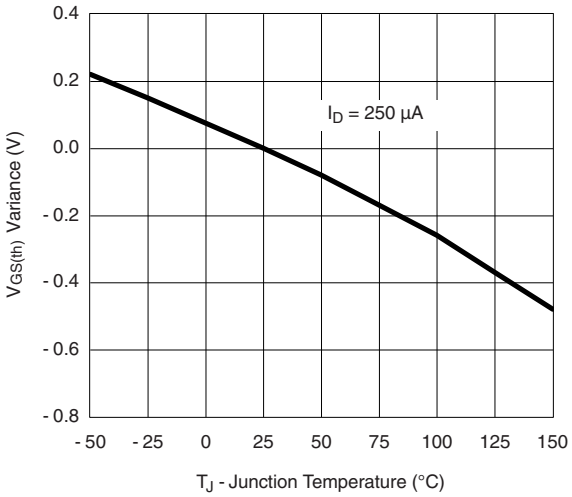
N-CHANNEL TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



Source-Drain Diode Forward Voltage

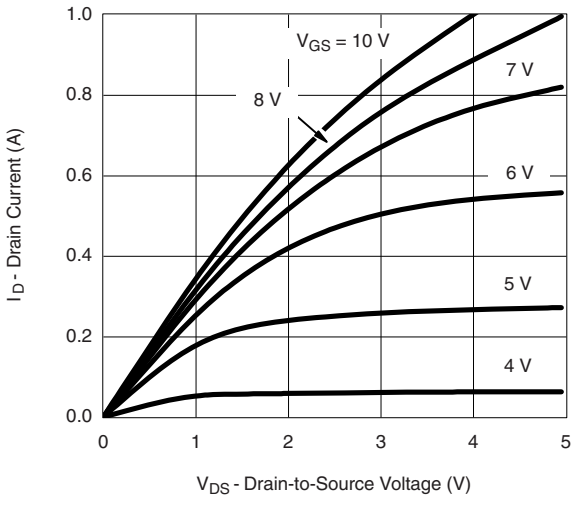


On-Resistance vs. Gate-to-Source Voltage

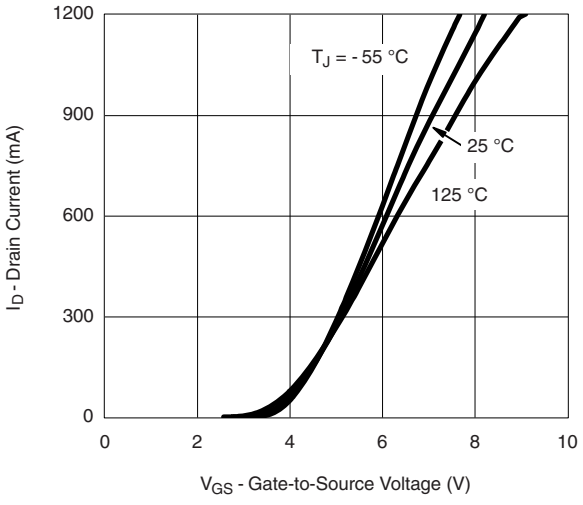


Threshold Voltage Variance Over Temperature

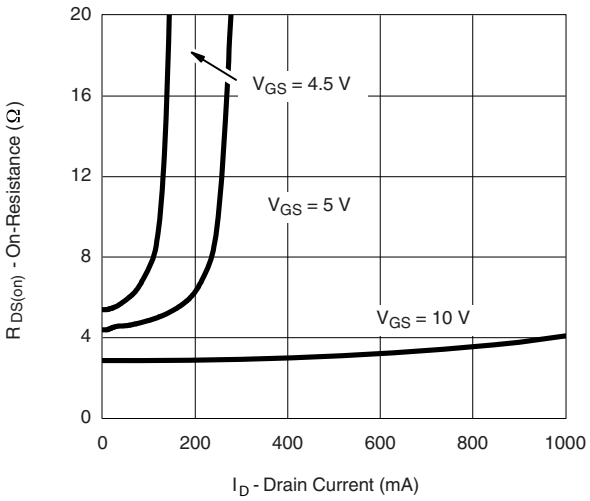
P-CHANNEL TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



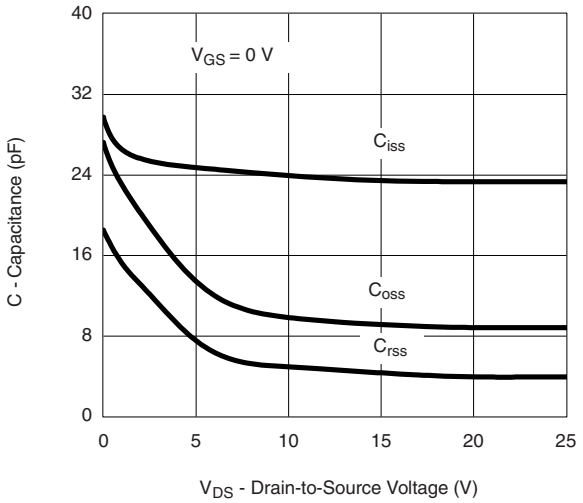
Output Characteristics



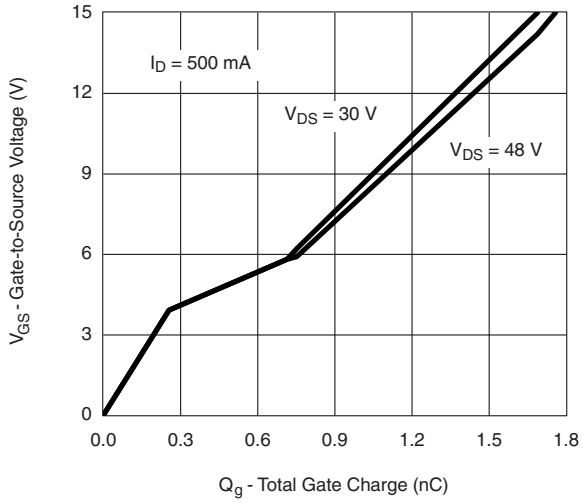
Transfer Characteristics



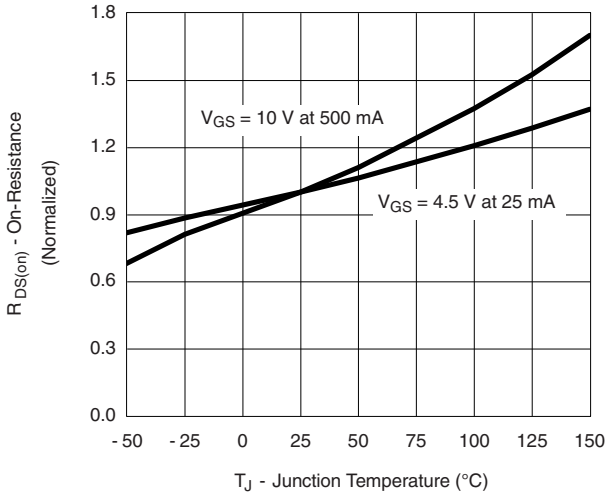
On-Resistance vs. Drain Current



Capacitance

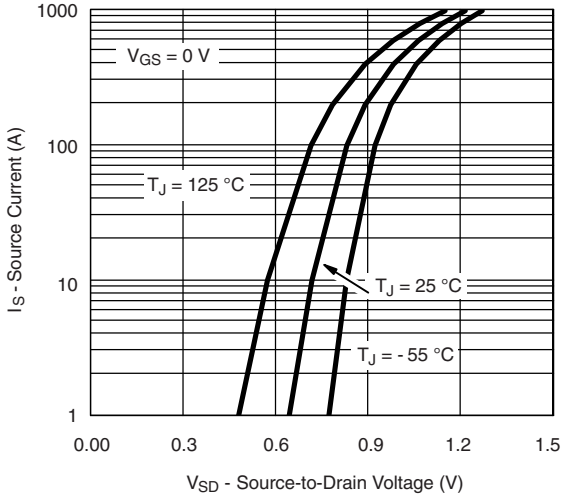


Gate Charge

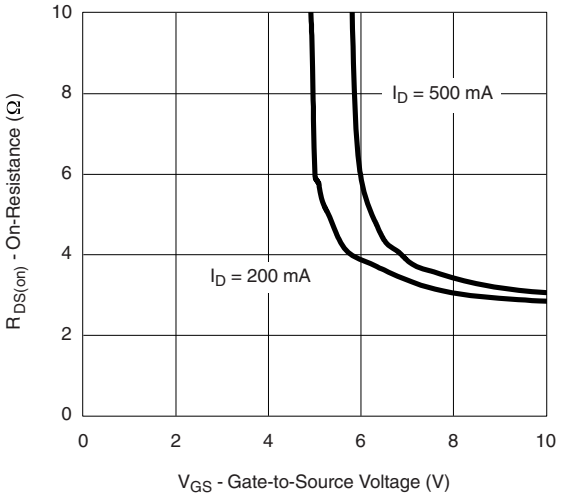


On-Resistance vs. Junction Temperature

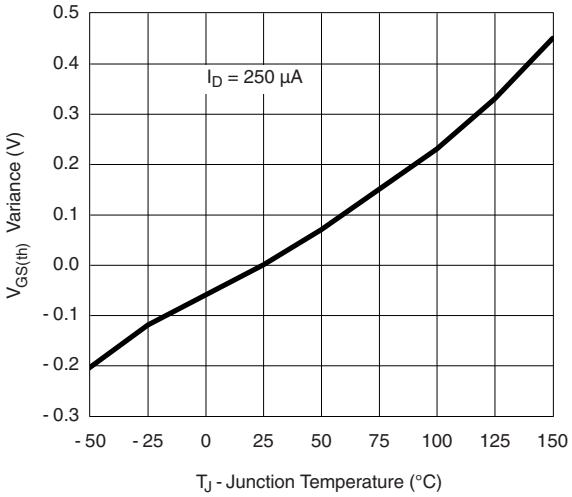
P-CHANNEL TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



Source-Drain Diode Forward Voltage

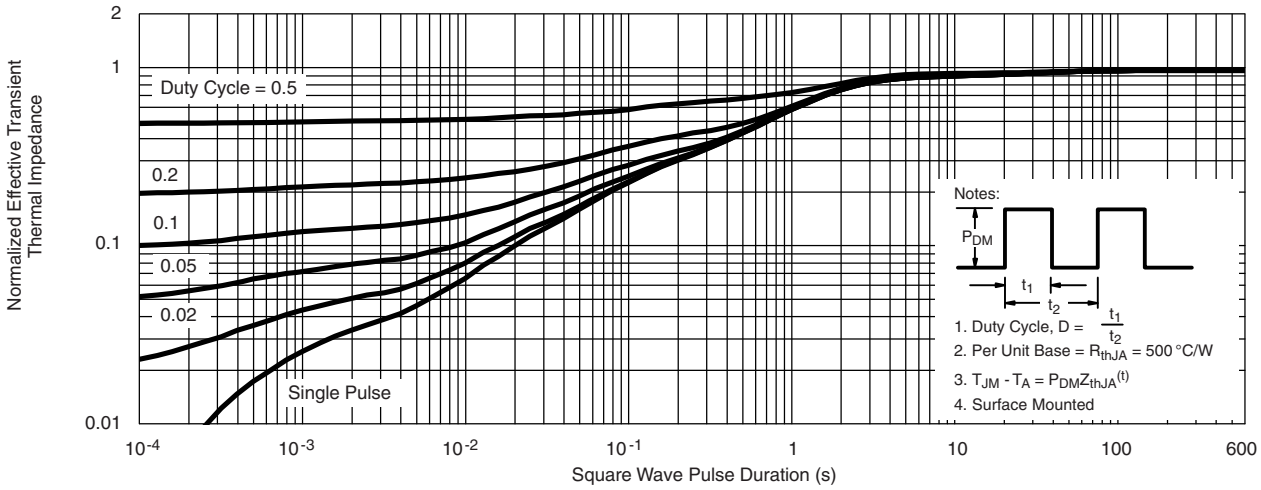


On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage Variance Over Temperature

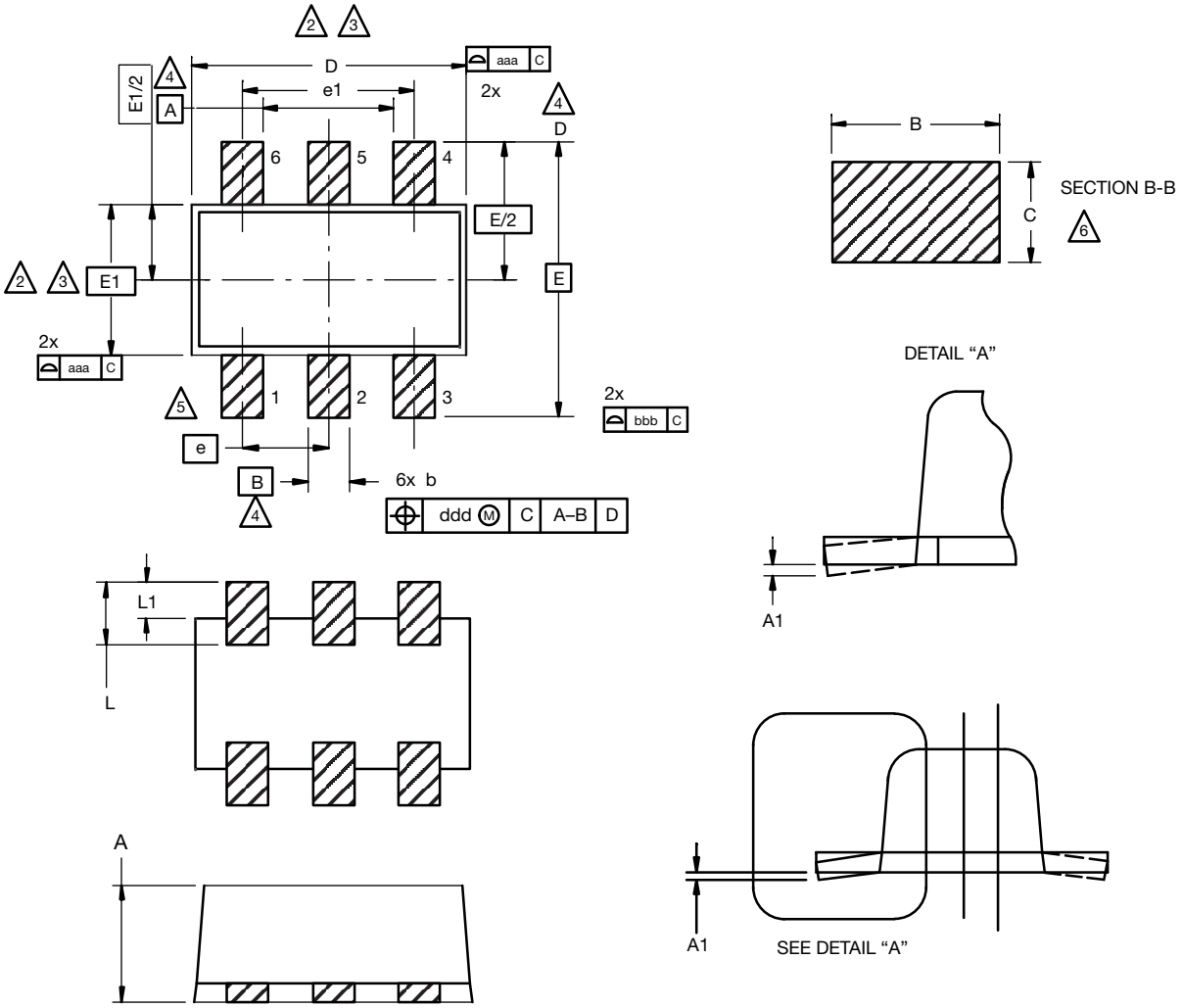
N- OR P-CHANNEL TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?71435.

SC-89 6-Leads (SOT-563F)



Notes

1. Dimensions in millimeters.

2. Dimension D does not include mold flash, protrusions or gate burrs. Mold flush, protrusions or gate burrs shall not exceed 0.15 mm per dimension E1 does not include interlead flash or protrusion, interlead flash or protrusion shall not exceed 0.15 mm per side.

3. Dimensions D and E1 are determined at the outmost extremes of the plastic body exclusive of mold flash, the bar burrs, gate burrs and interlead flash, but including any mismatch between the top and the bottom of the plastic body.

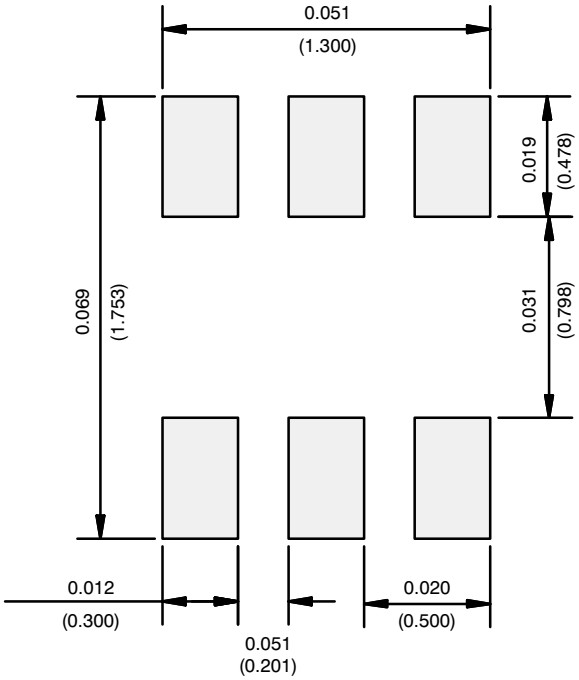
4. Datums A, B and D to be determined 0.10 mm from the lead tip.

5. Terminal numbers are shown for reference only.

6. These dimensions apply to the flat section of the lead between 0.08 mm and 0.15 mm from the lead tip.

DIM.	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.56	0.58	0.60
A1	0	0.02	0.10
b	0.15	0.22	0.30
c	0.10	0.14	0.18
D	1.50	1.60	1.70
E	1.50	1.60	1.70
E1	1.15	1.20	1.25
e	0.45	0.50	0.55
e1	0.95	1.00	1.05
L	0.25	0.35	0.50
L1	0.10	0.20	0.30
C14-0439-Rev. C, 11-Aug-14 DWG: 5880			

RECOMMENDED MINIMUM PADS FOR SC-89: 6-Lead



Recommended Minimum Pads
Dimensions in Inches/(mm)

Return to Index

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, “Vishay”), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay’s knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer’s responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and/or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer’s technical experts. Product specifications do not expand or otherwise modify Vishay’s terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

Material Category Policy

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as RoHS-Compliant fulfill the definitions and restrictions defined under Directive 2011/65/EU of The European Parliament and of the Council of June 8, 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment (EEE) - recast, unless otherwise specified as non-compliant.

Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as Halogen-Free follow Halogen-Free requirements as per JEDEC JS709A standards. Please note that some Vishay documentation may still make reference to the IEC 61249-2-21 definition. We confirm that all the products identified as being compliant to IEC 61249-2-21 conform to JEDEC JS709A standards.